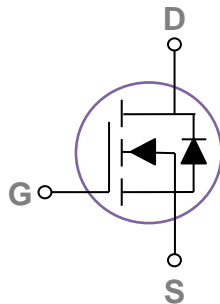
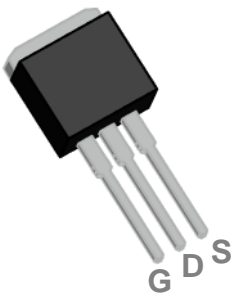


General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

TO262 Pin Configuration



BVDSS	RDSON	ID
100V	3.4mΩ	175A

Features

- 100V, 175A, $R_{DS(ON)} = 3.4m\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Networking
- Load Switch
- LED applications
- Quick Charger

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	175	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	110	A
I_{DM}	Drain Current – Pulsed ¹	700	A
EAS	Single Pulse Avalanche Energy ²	1250	mJ
IAS	Single Pulse Avalanche Current ²	50	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	290	W
	Power Dissipation – Derate above 25°C	2.32	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.43	$^\circ\text{C}/\text{W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	μA
		V _{DS} =80V, V _{GS} =0V, T _J =85°C	---	---	10	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A	---	2.8	3.4	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250μA	2	2.7	4	V

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{3, 4}	V _{DS} =50V, V _{GS} =10V, I _D =80A	---	92	135	nC
Q _{gs}	Gate-Source Charge ^{3, 4}		---	19	30	
Q _{gd}	Gate-Drain Charge ^{3, 4}		---	27	40	
T _{d(on)}	Turn-On Delay Time ^{3, 4}	V _{DD} =50V, V _{GS} =10V, R _G =6Ω I _D =80A	---	20	30	ns
T _r	Rise Time ^{3, 4}		---	15	23	
T _{d(off)}	Turn-Off Delay Time ^{3, 4}		---	60	90	
T _f	Fall Time ^{3, 4}		---	130	195	
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, F=1MHz	---	5600	8400	pF
C _{oss}	Output Capacitance		---	1200	1800	
C _{rss}	Reverse Transfer Capacitance		---	6	9	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	2	---	Ω

Guaranteed Avalanche Energy

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy	V _{DD} =50V, L=1mH, I _{AS} =25A	312	---	---	mJ

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	175	A
I _{SM}	Pulsed Source Current		---	---	350	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V
t _{rr}	Reverse Recovery Time	V _R =100V, I _S =10A	---	210	---	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs, T _J =25°C	---	600	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=50V, V_{GS}=10V, L=1mH, I_{AS}=50A, R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

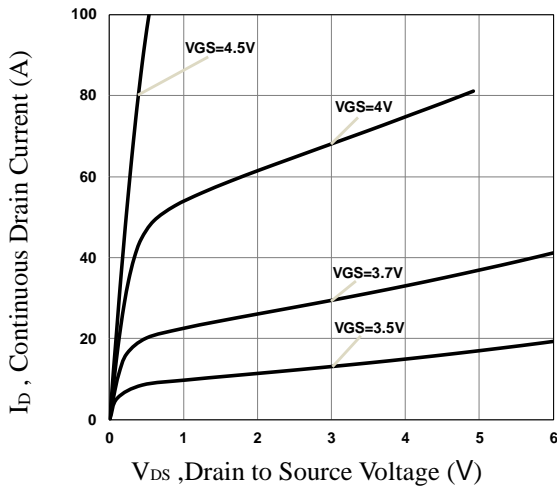


Fig.1 Typical Output Characteristics

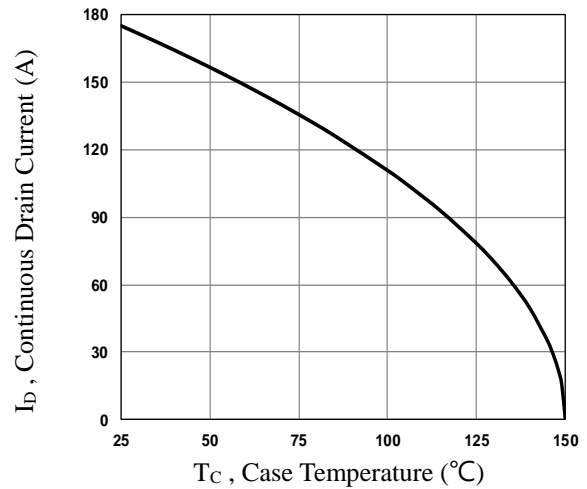


Fig.2 Continuous Drain Current vs. T_c

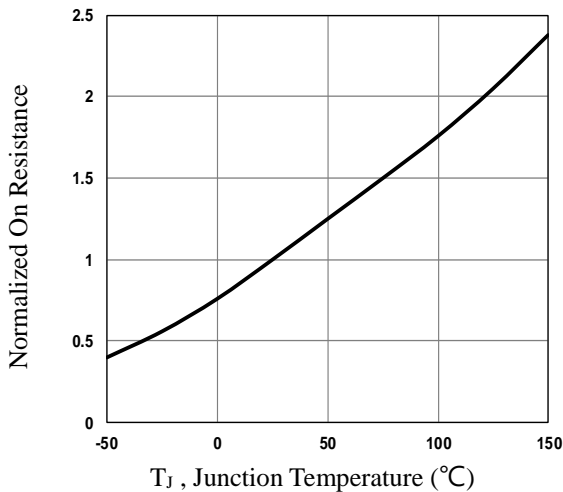


Fig.3 Normalized R_{DS(on)} vs. T_j

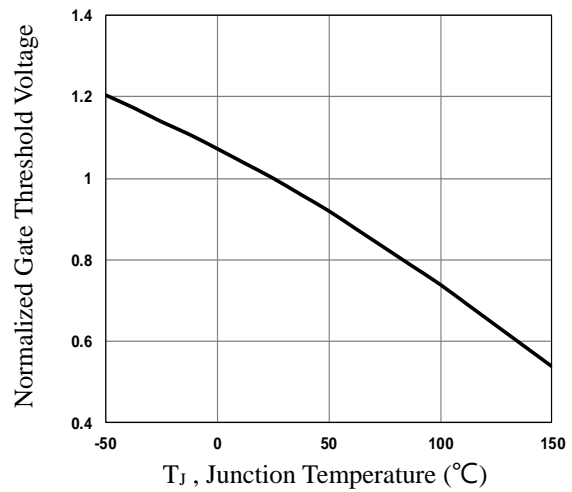


Fig.4 Normalized V_{th} vs. T_j

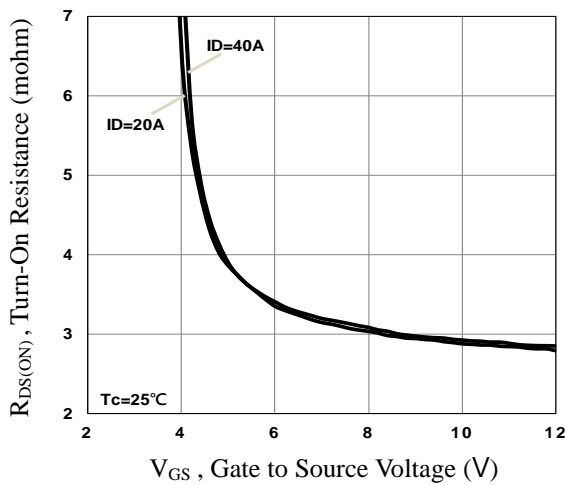


Fig.5 Turn-On Resistance vs. V_{GS}

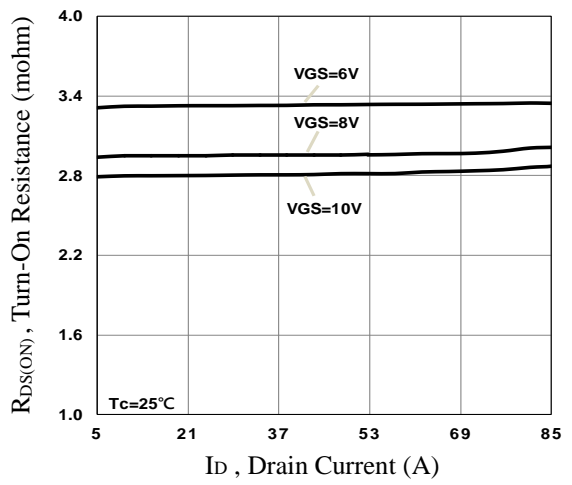


Fig.6 Turn-On Resistance vs. I_D

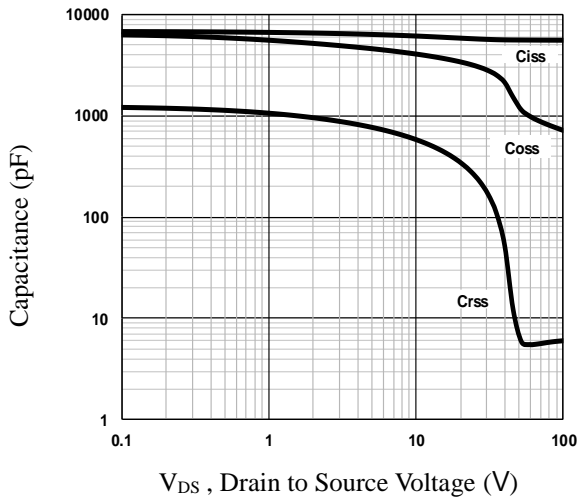


Fig.7 Capacitance Characteristics

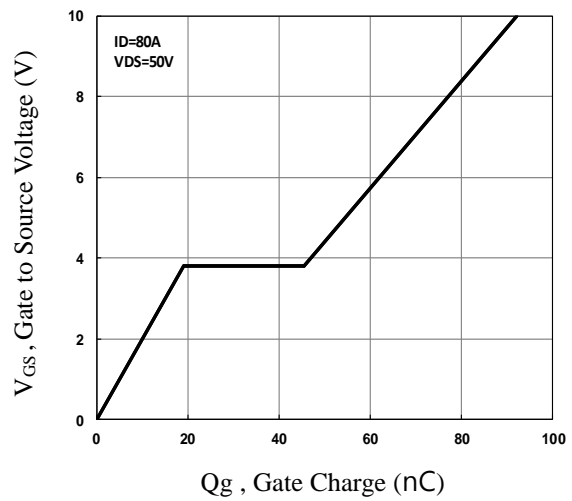


Fig.8 Gate Charge Characteristics

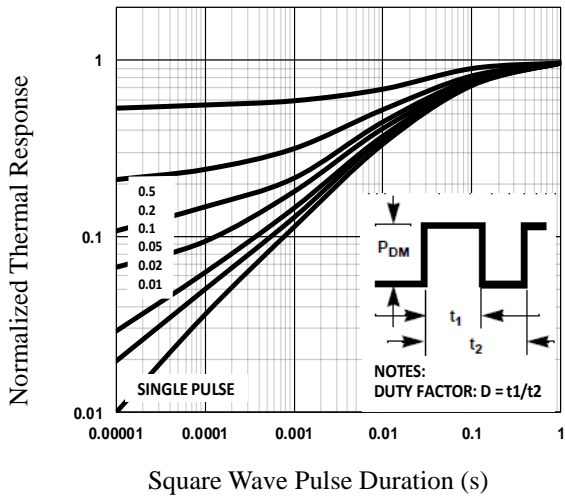


Fig.9 Normalized Transient Impedance

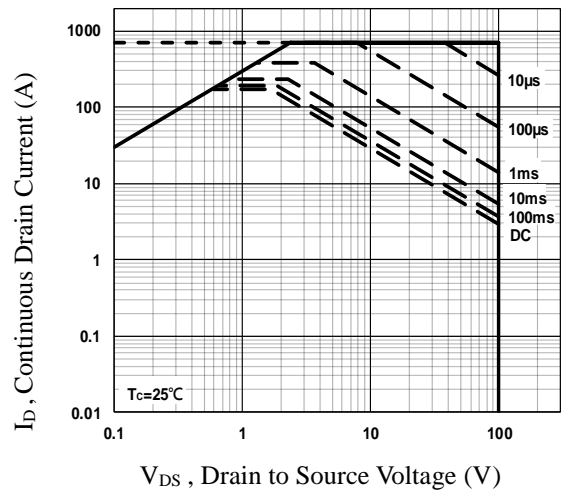


Fig.10 Maximum Safe Operation Area

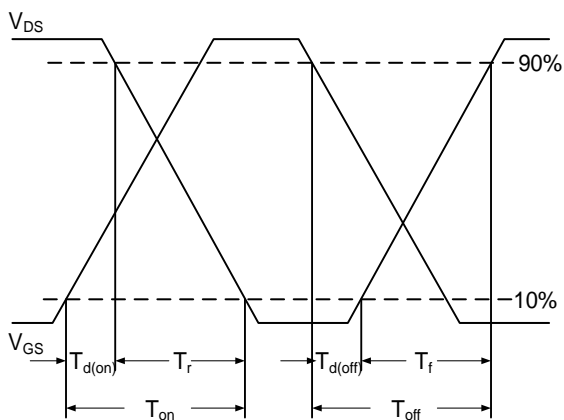


Fig.11 Switching Time Waveform

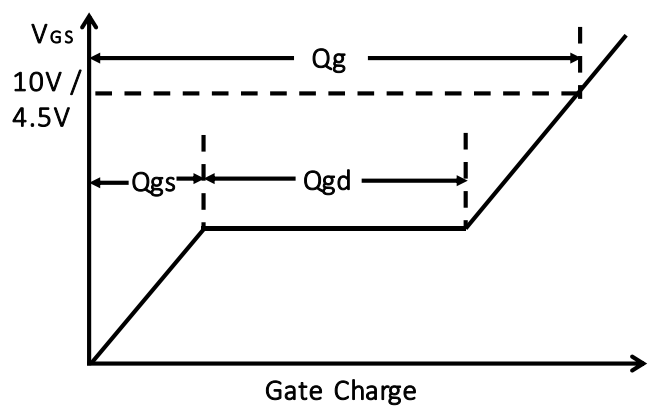
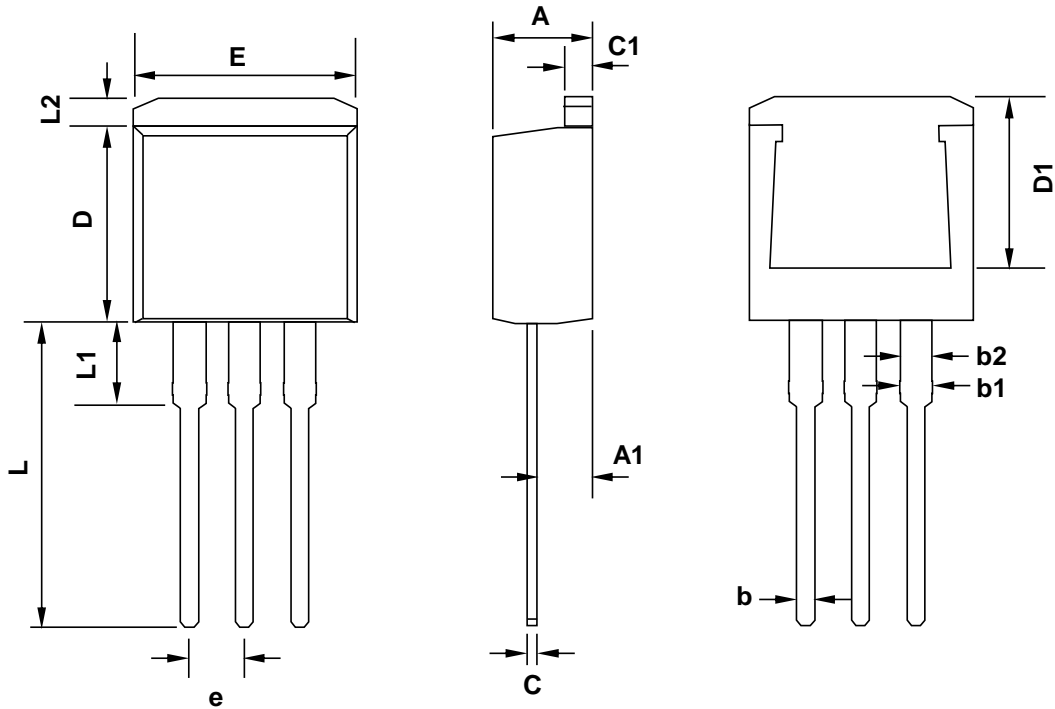


Fig.12 Gate Charge Waveform

TO262 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Max	Min	Max	Min
A	4.900	4.240	0.193	0.167
A1	2.850	2.300	0.112	0.091
b	0.910	0.700	0.036	0.028
b1	1.750	1.070	0.069	0.042
b2	1.700	1.070	0.067	0.042
C	0.600	0.280	0.024	0.011
C1	1.400	1.150	0.055	0.045
D	9.020	8.450	0.355	0.333
D1	---	6.600	---	0.260
E	10.40	9.960	0.409	0.392
e	2.540 BSC		0.100 BSC	
L	14.20	13.47	0.559	0.530
L1	4.000	3.550	0.157	0.140
L2	1.360 REF.		0.054 REF.	